TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74HCU04AP, TC74HCU04AF, TC74HCU04AFN

HEX INVERTER

The TC74HCU04A is a high speed CMOS INVERTER fabricated with silicon gate C^2MOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

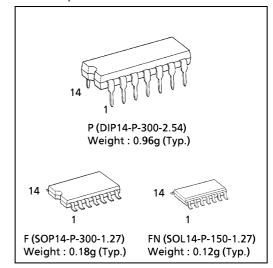
Since the internal circit is composed of a single stage inverter, it can be used in analog applications such as crystal oscillators.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

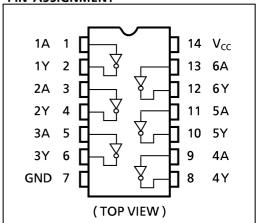
FEATURES:

- High Speed······ t_{pd} = 4ns(typ.) at V_{CC} = 5V
- Low Power Dissipation ······· $I_{CC} = 1 \mu A(Max.)$ at Ta = 25°C
- High Noise Immunity $V_{NIH} = V_{NIH} = 10\% V_{CC}$ (Min.)
- Output Drive Capability 10 LSTTL Loads
- Symmetrical Output Impedance··· | I_{OH} | = I_{OL} = 4mA(Min.)
- Balanced Propagation Delays $\cdots t_{pLH} \simeq t_{pHL}$
- Wide Operating Voltage Range ·· VCC(opr.) = 2V~6V
- Pin and Function Compatible with 74LS04

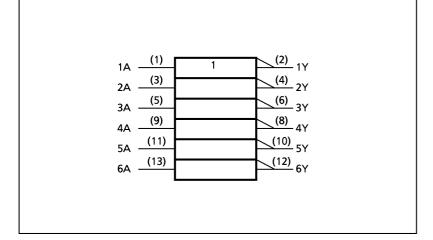
(Note) The JEDEC SOP (FN) is not available in Japan.



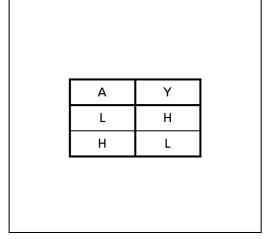
PIN ASSIGNMENT



IEC LOGIC SYMBOL



TRUTH TABLE



961001EBA2

● TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

ABSOLUTE MAXIMUM RATINGS

| PARAMETER | SYMBOL | VALUE | UNIT |
|-------------------------------------|------------------|--------------------------|------|
| Supply Voltage Range | V _{cc} | − 0.5~7 | V |
| DC Input Voltage | V _{IN} | $-0.5 \sim V_{CC} + 0.5$ | V |
| DC Output Voltage | V _{OUT} | $-0.5 \sim V_{CC} + 0.5$ | V |
| Input Diode Current | I _{IK} | ± 20 | mA |
| Output Diode Current | I _{OK} | ± 20 | mA |
| DC Output Current | I _{OUT} | ± 25 | mA |
| DC V _{CC} / Ground Current | I _{cc} | ± 50 | mA |
| Power Dissipation | P _D | 500 (DIP)* / 180 (SOP) | mW |
| Storage Temperature | T _{stg} | −65~150 | °C |

^{*500}mW in the range of Ta= $-40^{\circ}\text{C}\sim65^{\circ}\text{C}$. From Ta= 65°C to 85°C a derating factor of $-10\text{mW}/^{\circ}\text{C}$ shall be applied until 300mW.

RECOMMENDED OPERATING CONDITIONS

| PARAMETER | SYMBOL | VALUE | UNIT |
|-----------------------|------------------|-------------------|----------|
| Supply Voltage | V _{cc} | 2~6 | V |
| Input Voltage | V _{IN} | 0∼V _{cc} | V |
| Output Voltage | V _{OUT} | 0∼V _{cc} | ٧ |
| Operating Temperature | T _{opr} | −40~85 | Ç |

DC ELECTRICAL CHARACTERISTICS

| PARAMETER | SYMBOL | TEST CONDITION | | V _{cc} | V _{cc} Ta = 25 | | С | $Ta = -40 \sim 85$ °C | | UNIT |
|--------------------------------|-------------------|--------------------------------------|--|-------------------|-------------------------|-------------------|-------------------|-----------------------|-------------------|---------|
| FARAIVIETER SYMBOL | | TEST CONDITION | | (V) | MIN. | TYP. | MAX. | MIN. | MAX. | וואוט |
| High - Level Input Voltage | V _{IH} | | | 2.0 4.5 6.0 | 1.7 3.6 4.8 | _ _ _ | _ _ _ | 1.7 3.6 4.8 | _ _ _ | v |
| Low - Level Input Voltage | V _{IL} | | | 2.0 4.5 6.0 | | _ _ _ | 0.3 0.9 1.2 | | 0.3 0.9 1.2 | V |
| High - Level Output Voltage | V _{OH} | $V_{IN} = V_{IL}$ | $I_{OH} = -20\mu A$ | 2.0 4.5 6.0 | 1.8 4.0 5.5 | 2.0 4.5 5.9 | _ _ _ | 1.9 4.4 5.9 | _ _ _ | v |
| | | V _{IN} = GND | $I_{OH} = -4 \text{ mA}$ $I_{OH} = -5.2 \text{ mA}$ | 4.5 6.0 | 4.18 5.68 | 4.31 5.80 | _ | 4.13 5.63 | _ | |
| Low - Level Output Voltage | V _{OL} | $V_{IN} = V_{IH}$ | I _{OL} = 20μΑ | 2.0 4.5 6.0 | _ _ _ | 0.0 0.0 0.1 | 0.2 0.5 0.5 | _ _ _ | 0.2 0.5 0.5 | v |
| | $V_{IN} = V_{CC}$ | $I_{OL} = 4$ mA $I_{OL} = 5.2$ mA | 4.5 6.0 | _ _ | 0.17 0.18 | 0.26 0.26 | <u>-</u> | 0.33 0.33 | | |
| Input Leakage Current | I _{I N} | $V_{IN} = V_{CC}$ or GND | | 6.0 | _ | _ | ±0.1 | _ | ± 1.0 | |
| Quiescent Supply Current | I _{CC} | $V_{IN} = V_{CC}$ or GND | | 6.0 | _ | _ | 1.0 | _ | 10.0 | μA |

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AC ELECTRICAL CHARACTERISTICS ($C_L = 15pF$, $V_{CC} = 5V$, Ta = 25°C, Input $t_r = t_f = 6ns$)

| PARAMETER | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
|------------------------|--------------------------------------|----------------|------|------|------|------|
| Output Transition Time | t _{TLH} t _{THL} | | _ | 4 | 8 | ns |
| Propagation Delay Time | t _{pLH} t _{pHL} | | _ | 4 | 8 | 113 |

AC ELECTRICAL CHARACTERISTICS ($C_L = 50pF$, Input $t_r = t_f = 6ns$)

| PARAMETER | SYMBOL | TEST CONDITION | | Ta = 25°C | | 2 | Ta = -40~85°C | | UNIT |
|-------------------------------|---------------------|----------------|-------------|-----------|------|------|---------------|------|------|
| | | TEST CONDITION | $V_{cc}(V)$ | MIN. | TYP. | MAX. | MIN. | MAX. | |
| | t _{TLH} | | 2.0 | _ | 30 | 75 | _ | 95 | |
| Output Transition Time | | | 4.5 | _ | 8 | 15 | - | 19 | |
| | t _{THL} | | 6.0 | _ | 7 | 13 | _ | 16 | ns |
| Propagation Delay Time | + | | 2.0 | _ | 18 | 60 | _ | 75 | ''3 |
| | t _{pLH} | | 4.5 | _ | 6 | 12 | - | 15 | |
| | $	au_{pHL}$ | | 6.0 | 1 | 5 | 10 | _ | 13 | |
| Input Capacitance | C _{IN} | | | _ | 9 | 15 | _ | 15 | nE |
| Power Dissipation Capacitance | C _{PD} (1) | | | _ | 13 | _ | _ | _ | pF |

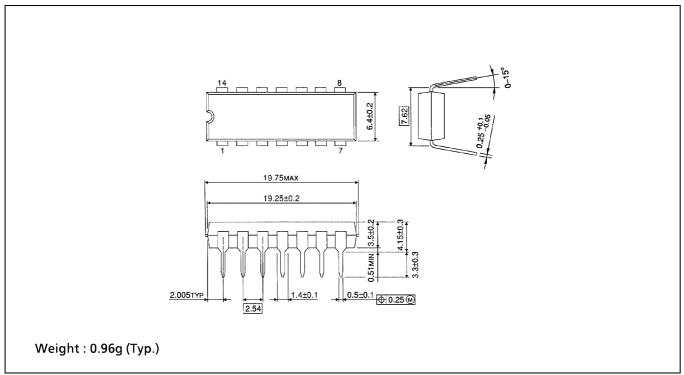
Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 I_{CC} (opr) = $C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 6$ (per Gate)

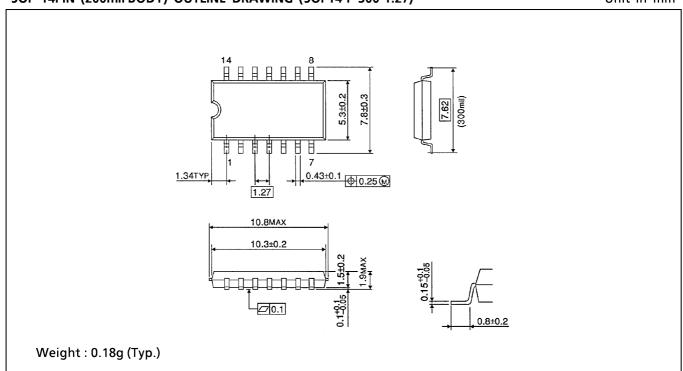
DIP 14PIN OUTLINE DRAWING (DIP14-P-300-2.54)

Unit in mm



SOP 14PIN (200mil BODY) OUTLINE DRAWING (SOP14-P-300-1.27)

Unit in mm



SOP 14PIN (150mil BODY) OUTLINE DRAWING (SOL14-P-150 -1.27)

Unit in mm

